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Mullish

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)
Hongyong ZHANG)
Serial No. 09/987,607) Art Unit: 2813
Filed: November 15, 2001) Examiner: D. Hogans
For: METHOD FOR PRODUCING)
SEMICONDUCTOR INTEGRATED)
CIRCUIT INCLUDING A THIN FILM) Date: January 21, 2003
TRANSISTOR AND A CAPACITOR)

PRELIMINARY AMENDMENT

Honorable Commissioner of Patents
Washington, D.C. 20231

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JAN 21 2003
OFFICE OF PETITIONS

Sir:

Please preliminarily amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 1-5 as follows:

- Sub
C17
of:
- B1
1. A method for manufacturing a semiconductor device comprising the steps of:
- forming an interlayer insulator comprising at least upper and lower layers, each comprising different dry etching characteristics;
 - etching the upper layer of the interlayer insulator using a first mask, wherein the lower layer of the interlayer insulator is used as an etching stopper;
 - forming a second mask to cover a portion of the lower layer of the interlayer insulator, which is exposed by the etching step; and
 - selectively etching the lower layer of the interlayer insulator using the second mask to form a contact hole.